Silicon N-Channel MOS FET

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Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for Switching regulator

Outline





Ordering Information

Туре No.	V _{DSS}
2SK2116	450 V
2SK2117	500 V

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK2116	V _{DSS}	450	V
	2SK2117	V _{DSS}	500	
Gate to source voltage		V _{GSS}	±30	V
Drain current		I _D	7	А
Drain peak current		↓ *1 D(pulse)	28	А
Body to drain diode reverse drain of	I _{DR}	7	А	
Channel dissipation		Pch* ²	35	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes 1. PW 10 µs, duty cycle 1 %

2. Value at Tc = 25 °C

Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK2116	$V_{(BR)DSS}$	450	_	_	V	$I_{\rm D} = 10 \text{ mA}, V_{\rm GS} = 0$
breakdown voltage	2SK2117		500				
Gate to source b voltage	reakdown	$V_{(\text{BR})\text{GSS}}$	±30	_	_	V	$I_{g} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source le	eak current	I _{GSS}		_	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate	2SK2116	I _{DSS}	_	_	250	μΑ	$V_{\rm DS} = 360 \text{ V}, V_{\rm GS} = 0$
voltage drain current	2SK2117						$V_{\rm DS} = 400 \ V, \ V_{\rm GS} = 0$
Gate to source c	utoff voltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to	2SK2116	$R_{DS(on)}$	_	0.6	0.8		$I_{\rm D} = 4$ A, $V_{\rm GS} = 10$ V ^{*1}
source on state resistance	2SK2117		_	0.7	0.9		
Forward transfer	admittance	y _{fs}	4.0	6.5	—	S	$I_{\rm D} = 4 \text{ A}$ $V_{\rm DS} = 10 \text{ V}^{*1}$
Input capacitance	е	Ciss		1050	_	pF	V _{DS} = 10 V
Output capacitance		Coss	_	280	_	pF	$V_{GS} = 0$
Reverse transfer	capacitance	Crss	_	40	_	pF	f = 1 MHz
Turn-on delay tin	ne	t _{d(on)}	—	15	—	ns	$I_{D} = 4 A$
Rise time		t,		55		ns	V _{GS} = 10 V
Turn-off delay tin	ne	t _{d(off)}	—	95	_	ns	$R_{L} = 7.5$
Fall time		t _f	—	40	—	ns	
Body to drain dio voltage	de forward	V_{DF}		0.95	_	V	$I_{\rm F} = 7 {\rm A}, {\rm V}_{\rm GS} = 0$
Body to drain dio recovery time	de reverse	t _{rr}		320	—	ns	$I_F = 7 \text{ A}, V_{GS} = 0,$ diF / dt = 100 A / µs

Note 1. Pulse Test

See characteristic curve of 2SK1157, 2SK1158.

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Package Dimensions



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